

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	("6903386").PN.	US-PGPUB; USPAT	OR	OFF	2005/06/07 08:17
L2	110	emitter with "III" with "VI"	US-PGPUB; USPAT	OR	ON	2005/06/07 08:32
L3	82	2 and @ad<"20020614"	US-PGPUB; USPAT	OR	ON	2005/06/07 08:32
L4	87	emitter with "III" with "VI"	USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 08:28
L5	1089	438/234,235,309,312.ccls.	US-PGPUB; USPAT	OR	ON	2005/06/07 08:35
L6	811	5 and @ad<"20020614"	US-PGPUB; USPAT	OR	ON	2005/06/07 08:35
L7	718	6 and emitter	US-PGPUB; USPAT	OR	ON	2005/06/07 08:32
L8	718	7 not 3	US-PGPUB; USPAT	OR	ON	2005/06/07 08:33
L9	1662	257/197,200.ccls.	US-PGPUB; USPAT	OR	ON	2005/06/07 08:35
L10	996	9 and @ad<"20020614"	US-PGPUB; USPAT	OR	ON	2005/06/07 08:35
L11	914	10 not 8	US-PGPUB; USPAT	OR	ON	2005/06/07 08:35

US-PAT-NO: 6049099

DOCUMENT-IDENTIFIER: US 6049099 A

TITLE: Cadmium sulfide layers for indium phosphide-based  
heterojunction bipolar transistors

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Detailed Description Text - DETX (7):

The CdS **emitter** layer 17 can be grown immediately following **III**-V compound growth in a specialized **III**-V/**II-VI** growth chamber or grown ex situ with a variety of techniques. CdS has been grown epitaxially on InP with several techniques: MBE, MOCVD, laser ablation, and chemical bath deposition (CBD). When an ex-situ growth process is used to deposit the CdS, all exposed **III**-V surfaces 13, 15, and 19 can be passivated with sulfur or CdS as described in U.S. Pat. No. #5,689,125 to Vaccaro et al., prior to performing the CdS growth. The CdS emitter 17 is n-type. Two known donor impurities in CdS are indium and boron.

US-PAT-NO: 5448077

DOCUMENT-IDENTIFIER: US 5448077 A

TITLE: Monolithic optical emitter-detector having a control  
amplifier with a feedback signal

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Brief Summary Text - BSTX (10):

One embodiment of the invention is an emitter and a detector optically coupled within a monolithic substrate. The emitter could be fabricated from groups III-V or II-VI material and the detector from PN or PIN materials.